

# MOSFET – N-Channel, UniFET™

**300 V, 38 A, 85 mΩ**

## FDA38N30

### Description

UniFET MOSFET is onsemi's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.

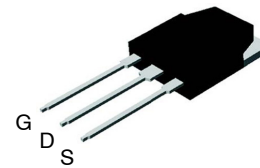
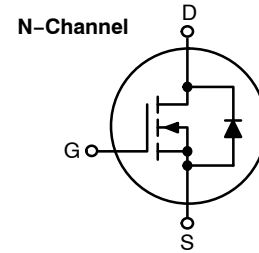
### Features

- $R_{DS(on)} = 70 \text{ m}\Omega$  (Typ.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 19 \text{ A}$
- Low Gate Charge (Typ. 60 nC)
- Low  $C_{rss}$  (Typ. 60 pF)
- 100% Avalanche Tested
- ESD Improved Capability
- RoHS Compliant

### Applications

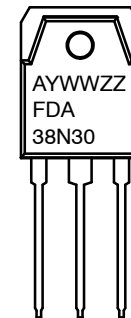
- PDP TV
- Uninterruptible Power Supply
- AC-DC Power Supply

| $V_{DS}$ | $R_{DS(on)} \text{ MAX}$ | $I_D \text{ MAX}$ |
|----------|--------------------------|-------------------|
| 300 V    | 85 mΩ @ 10 V             | 38 A              |



TO-3P-3LD / EIAJ SC-65, ISOLATED  
CASE 340BZ

### MARKING DIAGRAM



|          |                                |
|----------|--------------------------------|
| A        | = Assembly Site                |
| YWW      | = Date Code (Year & Work Week) |
| ZZ       | = Assembly Lot Number          |
| FDA38N30 | = Specific Device Code         |

### ORDERING INFORMATION

| Device   | Package   | Shipping         |
|----------|-----------|------------------|
| FDA38N30 | TO-3P-3LD | 450 Units / Tube |

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## MOSFET MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

| Symbol         | Parameter                                                            |                                            | Value       | Unit                |
|----------------|----------------------------------------------------------------------|--------------------------------------------|-------------|---------------------|
| $V_{DS}$       | Drain to Source Voltage                                              |                                            | 300         | V                   |
| $V_{GS}$       | Gate to Source Voltage                                               |                                            | $\pm 30$    | V                   |
| $I_D$          | Drain Current                                                        | - Continuous ( $T_C = 25^\circ\text{C}$ )  | 38          | A                   |
|                |                                                                      | - Continuous ( $T_C = 100^\circ\text{C}$ ) | 22          |                     |
|                |                                                                      | - Pulsed (Note 1)                          | 150         |                     |
| $I_{DM}$       |                                                                      |                                            |             |                     |
| $E_{AS}$       | Single Pulsed Avalanche Energy (Note 2)                              |                                            | 1200        | mJ                  |
| $I_{AR}$       | Avalanche Current (Note 1)                                           |                                            | 38          | A                   |
| $E_{AR}$       | Repetitive Avalanche Energy (Note 1)                                 |                                            | 31          | mJ                  |
| $dv/dt$        | Peak Diode Recovery $dv/dt$ (Note 3)                                 |                                            | 4.5         | V/ns                |
| $P_D$          | Power Dissipation                                                    | $T_C = 25^\circ\text{C}$                   | 312         | W                   |
|                |                                                                      | -Derate above $= 25^\circ\text{C}$         | 2.5         | W/ $^\circ\text{C}$ |
| $T_J, T_{STG}$ | Operating and Storage Temperature Range                              |                                            | -55 to +150 | $^\circ\text{C}$    |
| $T_L$          | Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds |                                            | 300         | $^\circ\text{C}$    |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2.  $L = 1.7\text{ mH}$ ,  $I_{AS} = 38\text{ A}$ ,  $V_{DD} = 50\text{ V}$ ,  $R_G = 25\ \Omega$ , starting  $T_J = 25^\circ\text{C}$ .
3.  $I_{SD} \leq 38\text{ A}$ ,  $di/dt \leq 200\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , starting  $T_J = 25^\circ\text{C}$ .

## THERMAL CHARACTERISTICS

| Symbol          | Parameter                                     | Value | Unit                      |
|-----------------|-----------------------------------------------|-------|---------------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case, Max.    | 0.4   | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient, Max. | 40    |                           |

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## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
|--------|-----------|-----------------|-----|-----|-----|------|
|--------|-----------|-----------------|-----|-----|-----|------|

### OFF CHARACTERISTICS

|                                      |                                           |                                                                       |     |     |      |      |
|--------------------------------------|-------------------------------------------|-----------------------------------------------------------------------|-----|-----|------|------|
| BV <sub>DSS</sub>                    | Drain to Source Breakdown Voltage         | I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0 V, T <sub>C</sub> = 25°C | 300 | –   | –    | V    |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | I <sub>D</sub> = 250 μA, referenced to 25°C                           | –   | 0.3 | –    | V/°C |
| I <sub>DSS</sub>                     | Zero Gate Voltage Drain Current           | V <sub>DS</sub> = 300 V, V <sub>GS</sub> = 0 V                        | –   | –   | 1    | μA   |
|                                      |                                           | V <sub>DS</sub> = 240 V, T <sub>C</sub> = 125°C                       | –   | –   | 10   |      |
| I <sub>GSS</sub>                     | Gate to Body Leakage Current              | V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0 V                        | –   | –   | ±100 | nA   |

### ON CHARACTERISTICS

|                     |                                   |                                                             |     |       |       |   |
|---------------------|-----------------------------------|-------------------------------------------------------------|-----|-------|-------|---|
| V <sub>GS(th)</sub> | Gate Threshold Voltage            | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA | 3.0 | –     | 5.0   | V |
| R <sub>DS(on)</sub> | Static Drain–Source On–Resistance | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 19 A               | –   | 0.070 | 0.085 | Ω |
| g <sub>FS</sub>     | Forward Transconductance          | V <sub>DS</sub> = 20 V, I <sub>D</sub> = 19 A               | –   | 6.3   | –     | S |

### DYNAMIC CHARACTERISTICS

|                     |                               |                                                                                 |   |      |   |    |
|---------------------|-------------------------------|---------------------------------------------------------------------------------|---|------|---|----|
| C <sub>iss</sub>    | Input Capacitance             | V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz                        | – | 2600 | – | pF |
| C <sub>oss</sub>    | Output Capacitance            |                                                                                 | – | 500  | – | pF |
| C <sub>rss</sub>    | Reverse Transfer Capacitance  |                                                                                 | – | 60   | – | pF |
| Q <sub>g(tot)</sub> | Total Gate Charge at 10 V     | V <sub>DS</sub> = 240 V, I <sub>D</sub> = 38 A, V <sub>GS</sub> = 10 V (Note 4) | – | 60   | – | nC |
| Q <sub>gs</sub>     | Gate to Source Gate Charge    |                                                                                 | – | 17   | – | nC |
| Q <sub>gd</sub>     | Gate to Drain “Miller” Charge |                                                                                 | – | 28   | – | nC |

### SWITCHING CHARACTERISTICS

|                     |                     |                                                                                                        |   |     |     |    |
|---------------------|---------------------|--------------------------------------------------------------------------------------------------------|---|-----|-----|----|
| t <sub>d(on)</sub>  | Turn–On Delay Time  | V <sub>DD</sub> = 150 V, I <sub>D</sub> = 38 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 25 Ω (Note 4) | – | 53  | 69  | ns |
| t <sub>r</sub>      | Turn–On Rise Time   |                                                                                                        | – | 110 | 143 | ns |
| t <sub>d(off)</sub> | Turn–Off Delay Time |                                                                                                        | – | 118 | 153 | ns |
| t <sub>f</sub>      | Turn–Off Fall Time  |                                                                                                        | – | 54  | 70  | ns |

### DRAIN–SOURCE DIODE CHARACTERISTICS

|                 |                                                          |                                                                               |   |     |     |    |
|-----------------|----------------------------------------------------------|-------------------------------------------------------------------------------|---|-----|-----|----|
| I <sub>S</sub>  | Maximum Continuous Drain to Source Diode Forward Current |                                                                               | – | –   | 38  | A  |
| I <sub>SM</sub> | Maximum Pulsed Drain–Source Diode Forward Current        |                                                                               | – | –   | 150 | A  |
| V <sub>SD</sub> | Drain to Source Diode Forward Voltage                    | V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 38 A                                 | – | –   | 1.4 | V  |
| t <sub>rr</sub> | Reverse Recovery Time                                    | V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 38 A, dI <sub>F</sub> /dt = 100 A/μs | – | 315 | –   | ns |
| Q <sub>rr</sub> | Reverse Recovery Charge                                  |                                                                               | – | 4.0 | –   | μC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

TYPICAL PERFORMANCE CHARACTERISTICS

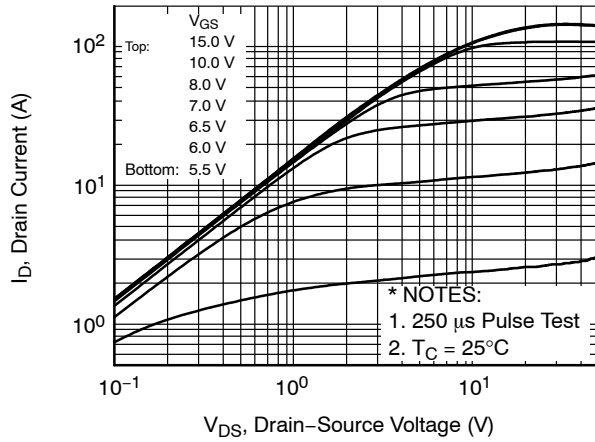


Figure 1. On-Region Characteristics

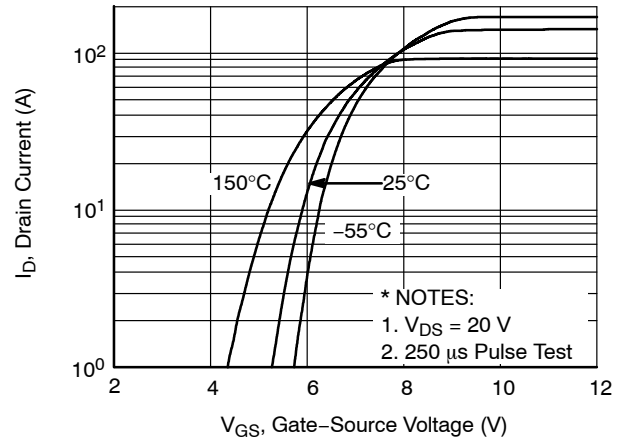


Figure 2. Transfer Characteristics

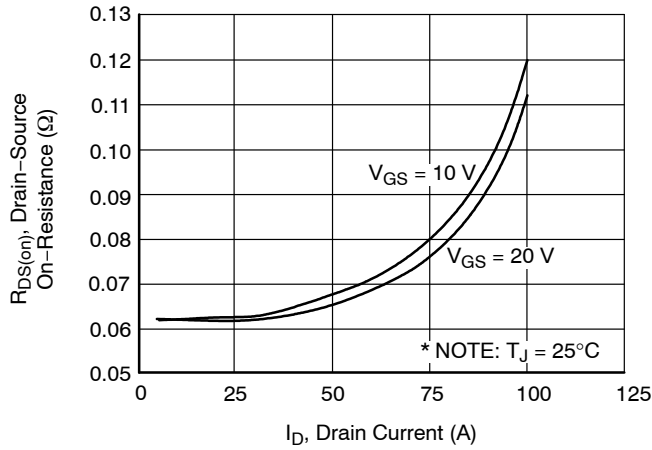


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

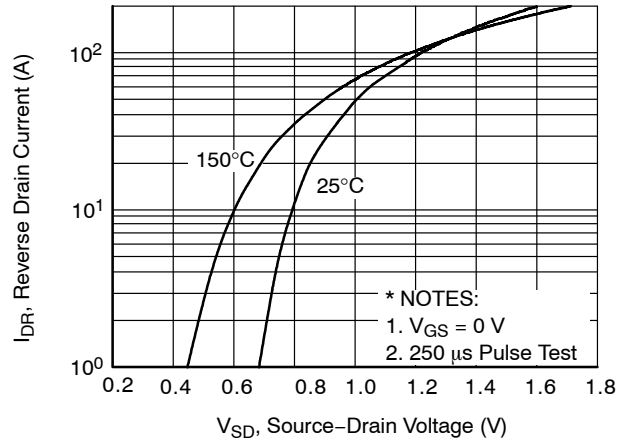


Figure 4. Body Diode Forward Voltage Variation vs. Source Current And Temperature

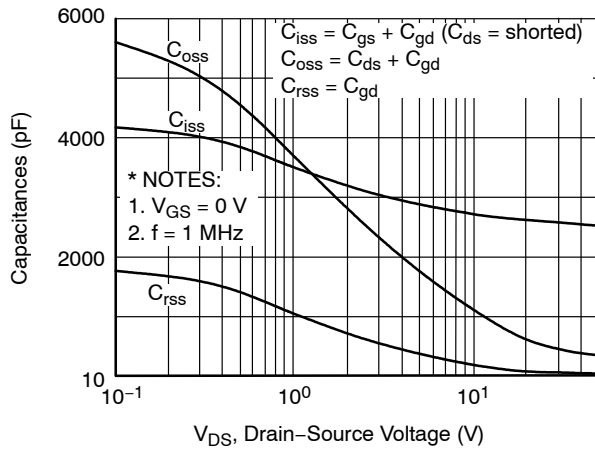


Figure 5. Capacitance Characteristics

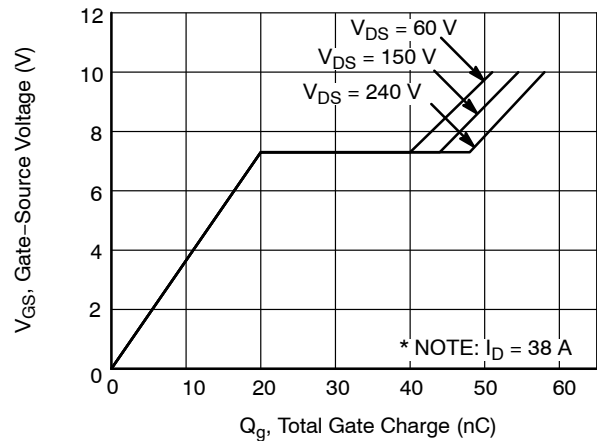
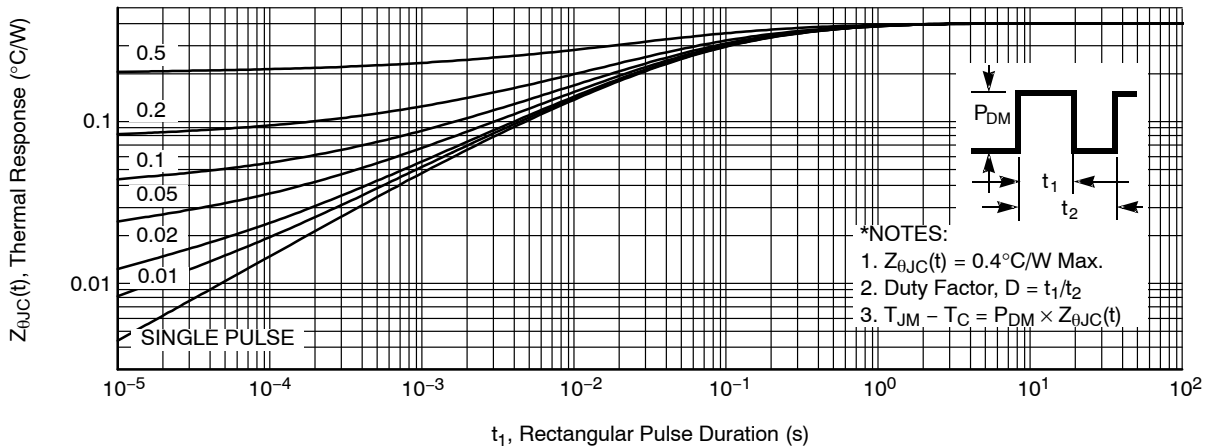
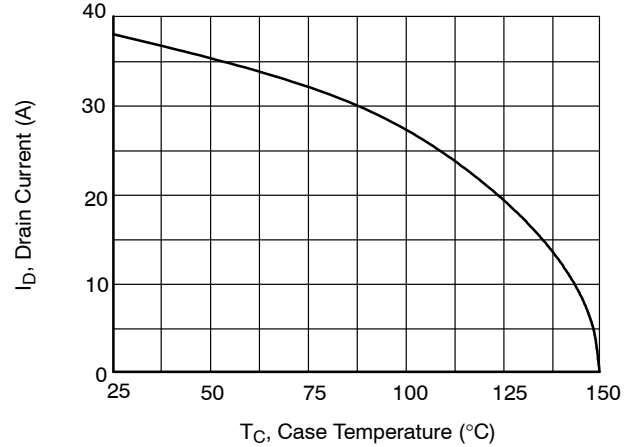
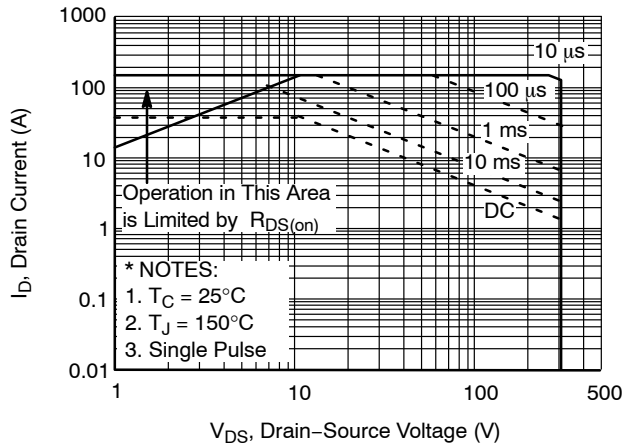
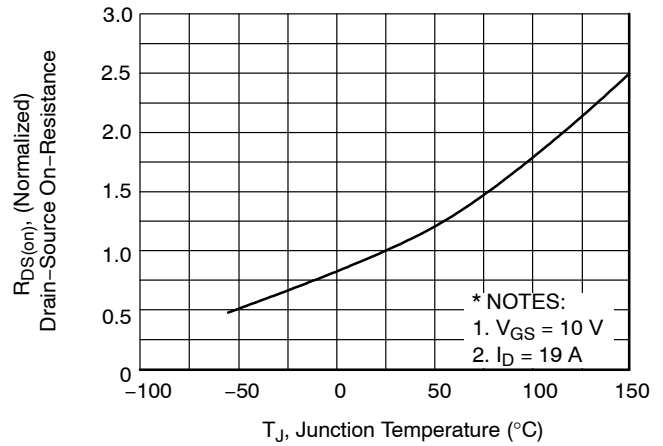
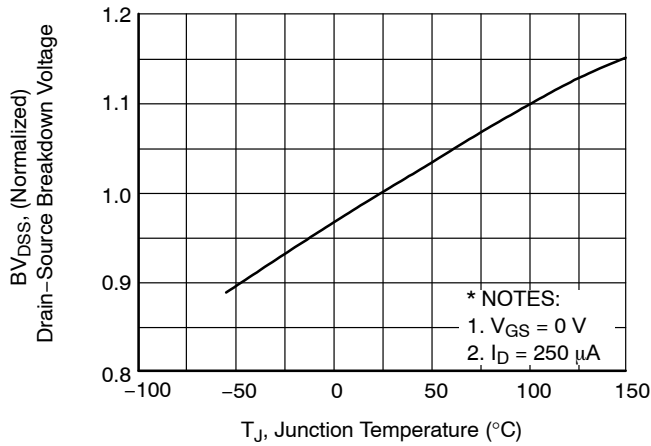


Figure 6. Gate Charge Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (continued)



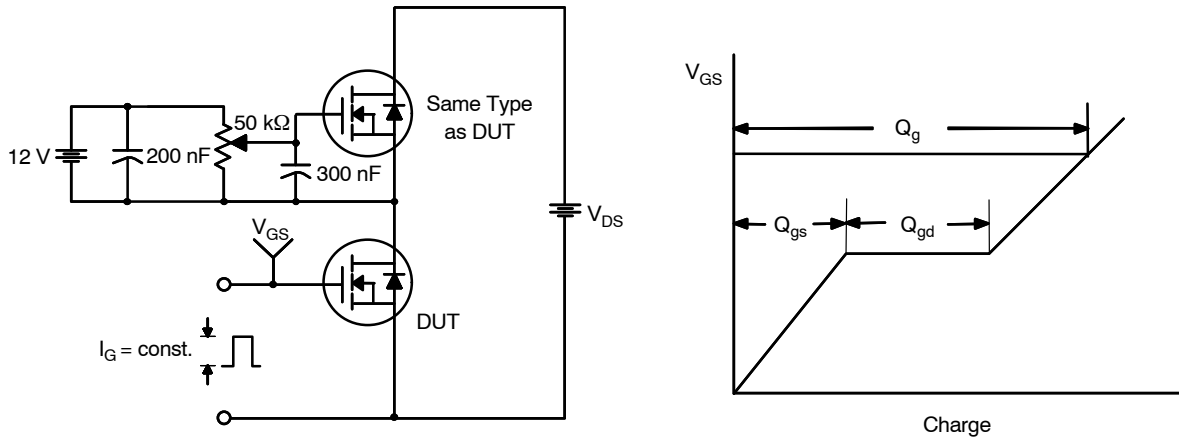


Figure 12. Gate Charge Test Circuit & Waveform

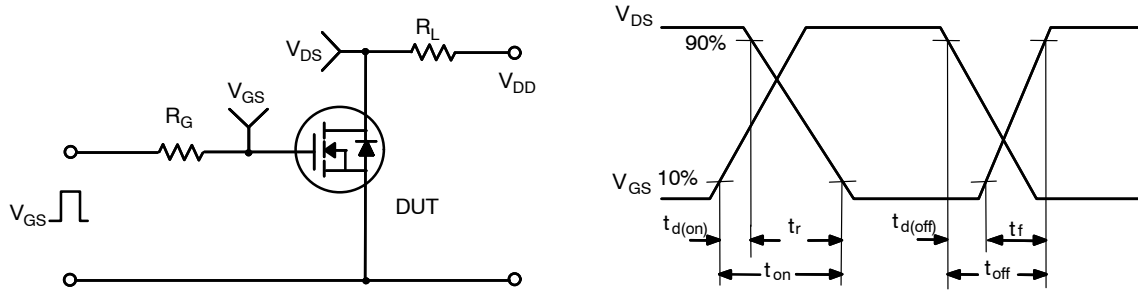


Figure 13. Resistive Switching Test Circuit & Waveforms

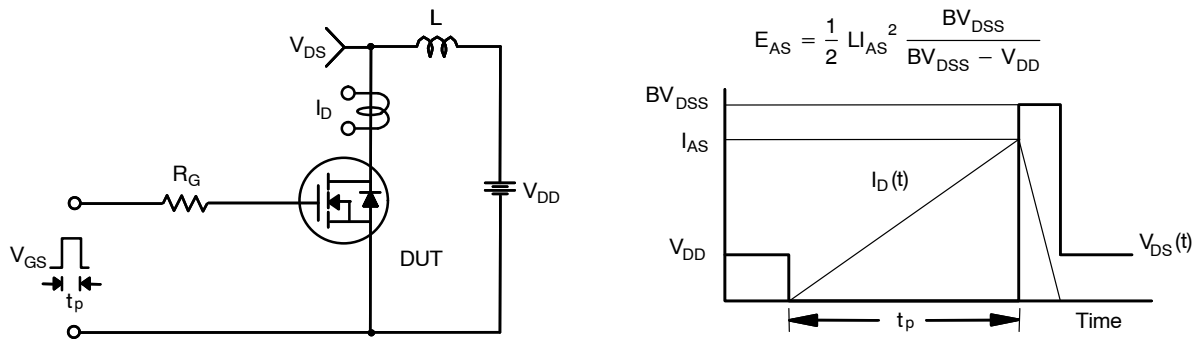
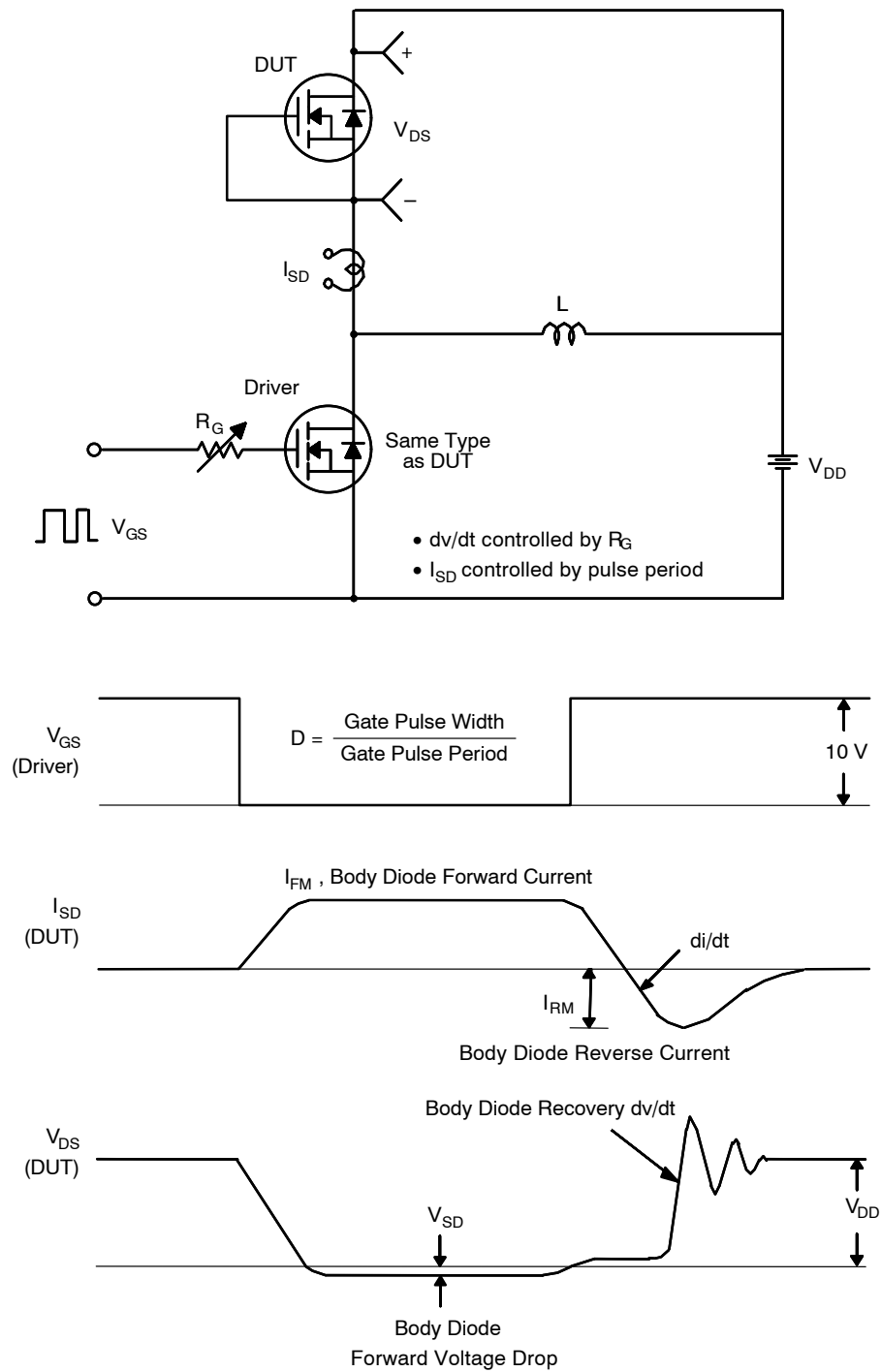


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

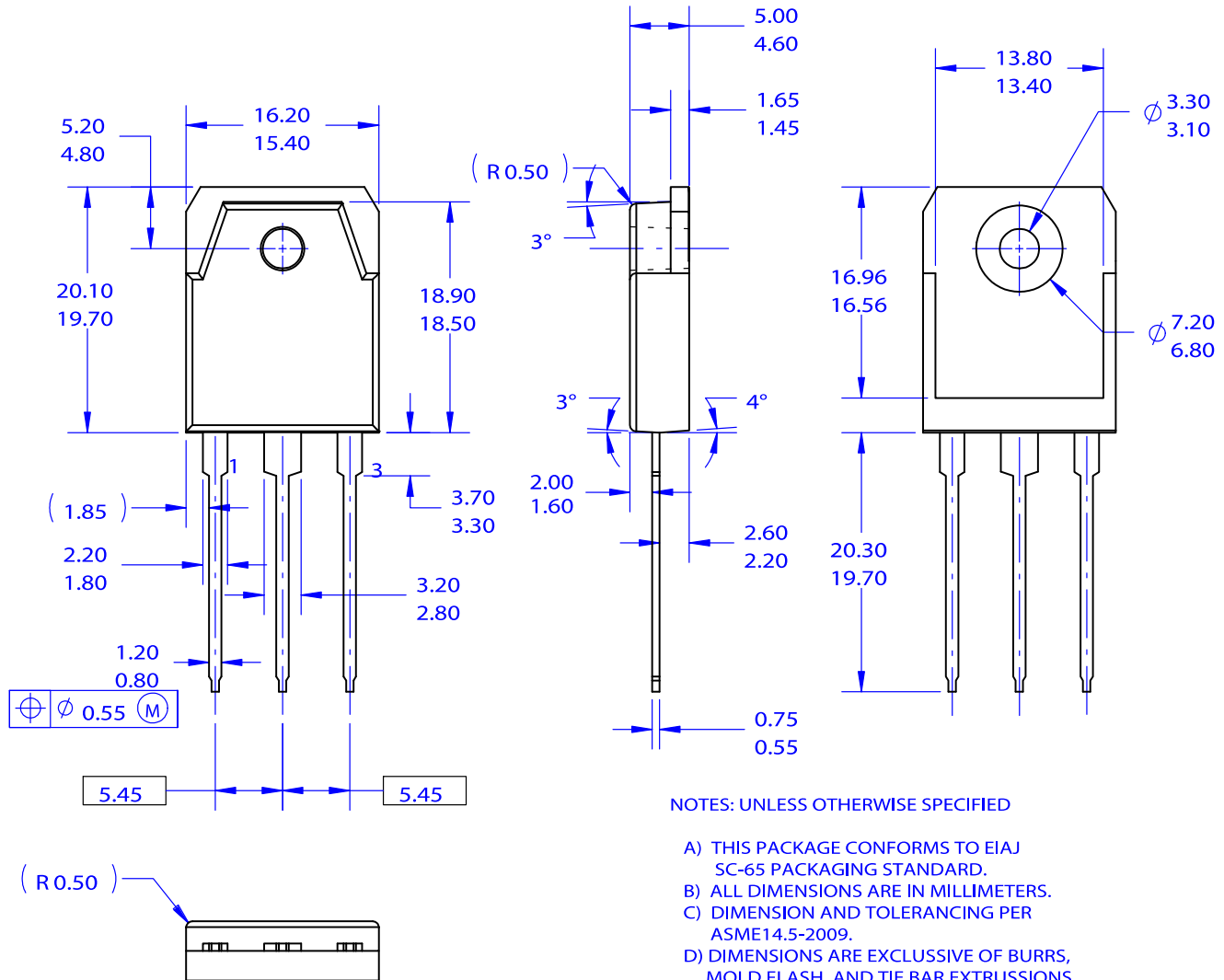
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**Figure 15. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms**

**TO-3P-3LD / EIAJ SC-65, ISOLATED**  
**CASE 340BZ**  
**ISSUE O**

DATE 31 OCT 2016



NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSION AND TOLERANCING PER ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.

|                         |                                         |                                                                                                                                                                                     |
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